



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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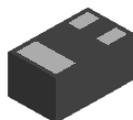
Features

- $BV_{CEO} > 45V$
- $I_C = 100mA$ High Collector Current
- $P_D = 1000mW$ Power Dissipation
- $0.60mm^2$ Package Footprint, 13 Times Smaller than SOT23
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type: BC857BLP4
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

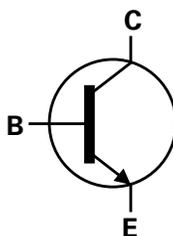
Mechanical Data

- Package: X2-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu. Solderable per MIL-STD-202, Method 208 Ⓔ4
- Weight: 0.0008 grams (Approximate)

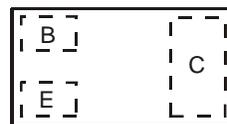
X2-DFN1006-3



Bottom View



Device Symbol



Top View
Device Schematic

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	100	mA
Peak Pulse Collector Current	I_{CM}	200	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	400	mW
		1000	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	310	$^\circ\text{C/W}$
		120	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	120	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CB0}	50	—	—	V	$I_C = 10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	45	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6	—	—	V	$I_E = 1\mu\text{A}, I_C = 0$
Collector-Cutoff Current	I_{CBO}	—	—	15 5	nA μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}, T_A = +150^\circ\text{C}$
DC Current Gain	h_{FE}	200	350	450	—	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	80 200	250 600	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	—	700 900	—	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5\text{mA}$
Base-Emitter Voltage (Note 9)	$V_{BE(on)}$	580	640 725	700 770	mV	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$ $V_{CE} = 5\text{V}, I_C = 10\text{mA}$
Gain Bandwidth Product	f_T	100	—	—	MHz	$V_{CE} = 5\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Collector-Base Capacitance	C_{cbo}	—	3	—	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

- Notes:
- For a device mounted on the minimum recommended pad layout of 2oz copper on a single-sided 1.6mm FR4 PCB; device is measured under still-air conditions whilst operating in steady-state condition.
 - Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 - Thermal resistance from junction to solder-point (on the exposed collector pad).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.
 - Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

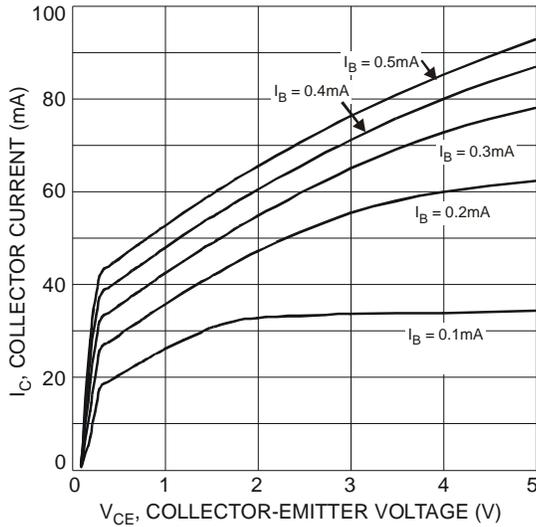


Figure 1. Typical Collector Current vs. Collector-Emitter Voltage

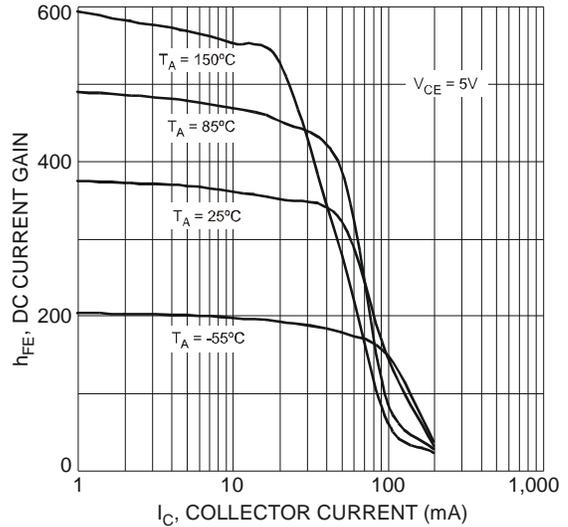


Figure 2. Typical DC Current Gain vs. Collector Current

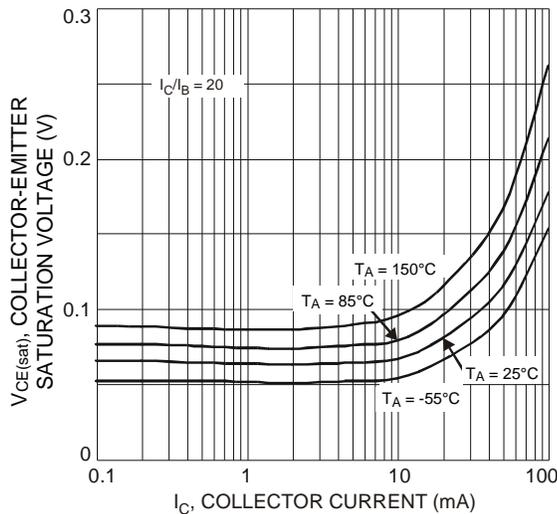


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current

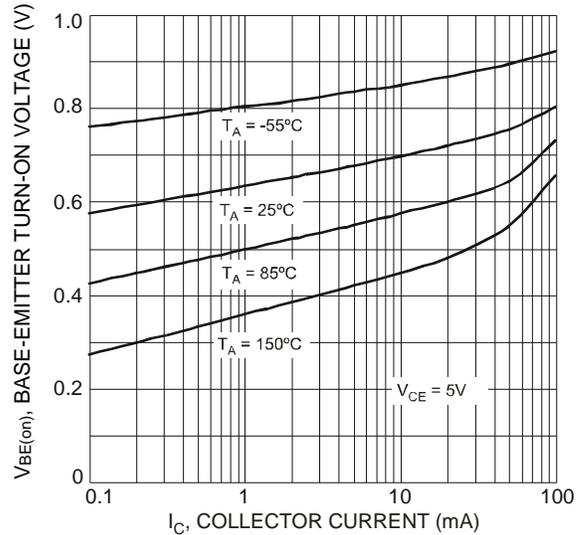


Figure 4. Typical Base-Emitter Turn-On Voltage vs. Collector Current

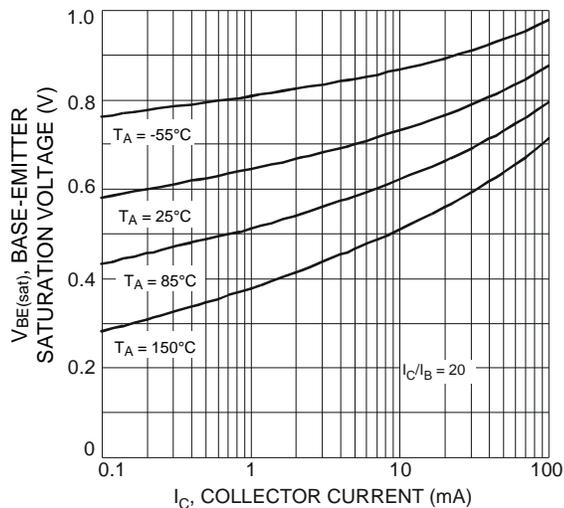
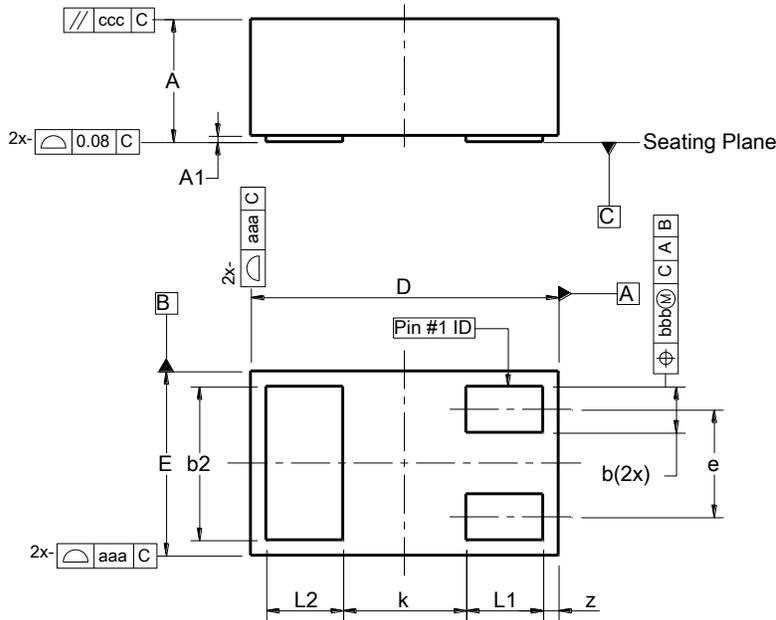


Figure 5. Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

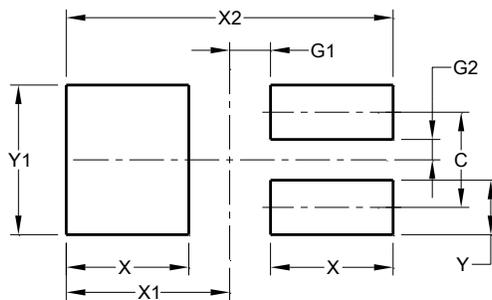
X2-DFN1006-3



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Dim	Min	Max	Typ
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
k	-	-	0.40
z	0.02	0.08	0.05
aaa	0.15		
bbb	0.05		
ccc	0.05		
All Dimensions in mm			

Suggested Pad Layout

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.350
G1	0.150
G2	0.075
X	0.450
X1	0.600
X2	1.200
Y	0.200
Y1	0.550